

Number	Hits	Search Text	DB	Time Stamp
1	1482	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
3	1482	"dual damascene" or dual adj damascene	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
4	1482	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and "dual damascene" or dual adj damascene	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
5	14	ash or ashing or ashed and "in-situ" and etch\$3 and "low-k"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
6	21	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and "organo silicate glass" or OSG	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
7	231	ash or ashing or ashed same "water vapor" or "H.sub.2O" same oxygen or "O.sub.2"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
8	28	ash or ashing or ashed same "water vapor" or "H.sub.2O" same oxygen or "O.sub.2" and "low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
9	1	8390096.pn.	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
11	58	dielectric same "organo silicate glass" or OSG or "black diamond"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
14	76	dielectric and "organo silicate glass" or OSG or "black diamond"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
15	24	dielectric and "organo silicate glass" or OSG	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
16	173	"dielectric constant" and "organo silicate glass" or OSG	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
24	3149	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and ash or ashing or ashed	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
25	1482	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and ash or ashing or ashed and 439 C.els.	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32
26	1482	"low-k" or dielectric or insulating and resist or photoresist or pattern or patterning or patterned and trench or via or contact or openings and etch\$3 and ash or ashing or ashed and 439 C.els. and "water vapor" or "H.sub.2O" and oxygen or "O.sub.2"	USPAT; EPO; JPO; IBM_TDB	2003/04/01 09:32

Search History 4:12 PM 04/01/2003

1: APR 01 2003 10:00:00 AM